

Stopping for Ion : **He** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Num
1965	Sattler, A. R. 'Ionization Produced by Energetic Silicon Atoms Within a Silicon Lattice' <i>Phys. Rev. A, 138, 1815-21 (1965)</i>	1965-Satt 0216
	<i>Comment : S. 21.2 - 3139 keV Si -> Si</i>	
1971	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. 'Energy Loss of H, D, and 4He Ions Channeled through Thin Single Crystals of Silicon' <i>Phys. Rev. Letters, 27, 1194-96 (1971)</i>	1971-Dell 0132
	<i>Comment : S. 0.9-5.0 MeV H, D, He -> Si Cryst. And Amorph.</i>	
1971	Thompson, D. A. Mackintosh, W. D. 'Stopping Cross Sections for 0.3 - 1.7 MeV Helium Ions in Silicon and Silicion Dioxide.' <i>J. Appl. Phys., 42, 3969-76 (1971)</i>	1971-Thom 0492
	<i>Comment : S. 0.3-L.7 MeV He -> Si, SiO2</i>	
1972	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. 'Transmission Energy Loss of Light Channeled Particles in Thin Silicon Single Crystals' <i>Rad. Effects, 13, 115-19 (1972)</i>	1972-Dell2 0480
	<i>Comment : S,dS. 0.9-5.0 MeV P, D, He -> Si (Cryst.)</i>	
1972	Eisen, F. H. Clark, G. J. Bottiger, J. Poate, J. M. 'Stopping Power of Energetic Helium Ions Transmitted through Thin Silicon Crystals in Channeling and Random Directions' <i>Rad. Effects, 13, 93-100 (1972)</i>	1972-Eise 0482
	<i>Comment : S,dS. 0.1-18 MeV He -> Si (Cryst.). Chan. And Random.</i>	
1973	Chu, W. K. Ziegler, J. F. Mitchell, I. V. Mackintosh, W. D. 'Energy-Loss Measurements of 4He Ions in Heavy Metals' <i>Appl. Phys. Letters, 22, 437-39 (1973)</i>	1973-Chu 3 0124
	<i>Comment : S. 2.0 MeV He -> Al, Si, V, Fe, Co, Ni, Cu, In, Ge, Mo, Sb, Te, Gd, Hf, Ta, W, Ir, Pt, Au, Pb</i>	
1973	Feng, J. S. -Y. Chu, W. K. Nicolet, M. -A. Mayer, J. W. 'Relative Measurements of Stopping Cross Section Factors by Back-Scattering' <i>Thin Solid Films, 19, 195-204 (1973)</i>	1973-Feng 0503
	<i>Comment : S (1-2 MeV) He -> Au, Ag, Cu, Al, Si. Relative Stopping</i>	
1973	Lin, W. K. Olson, H. G. Powers, D. 'Alpha-Particle Stopping Cross Sections of Silicon and Germanium' <i>J. Appl. Phys., 44, 3631-34 (1973)</i>	1973-Lin 0497
	<i>Comment : S. 0.3-2.0 MeV He -> Si, Ge (Amorph.)</i>	

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1973	Sellers, B. Hanser, A. Kelley, J. G. 'Energy Loss and Stopping Power Measurements Between 2 and 10 MeVamu for 3He and 4He in Silicon.' <i>Phys. Rev. B</i> , 8, 98-102 (1973) <i>Comment</i> : S. 6-30 MeV 3He, 8-40 MeV 4He -> Si (Cryst.?)	1973-Sell 0484
1973	Ziegler, J. F. Brodsky, M. H. 'Specific Energy Loss of 4He Ions in Silicon (Amorphous, Polycrystalline, and Single Crystal)' <i>J. Appl. Phys.</i> , 44, 188-96 (1973) <i>Comment</i> : S. 0.42-2.75 MeV He -> Si	1973-Zieg 0474
1974	Baglin, J. E. E. Ziegler, J. F. 'Tests of Bragg's Rule for Energy Loss of 4He Ions in Solid Compounds' <i>J. Appl. Phys.</i> , 45, 1413-1415 (1974) <i>Comment</i> : S. He (2 MeV) -> Si, Rh, Hf, Al, W, C, and many compounds	1974-Bagl 1583
1974	Schmid, K. Fischer, G. Muller, H. Ryssel, H. 'Experimental Data About Dechanneling and Channel Stopping Power' <i>Rad. Effects</i> , 23, 145-49 (1974) <i>Comment</i> : S. 1 MeV He -> Si (Cryst.)	1974-Schm 0519
1975	Bulgakov, Yu. V. Nikolaev, V. S. Shulga, V. I. 'Impact-Parameter Dependence of Inelastic Energy Losses for He and N Ions Channeled in Si' <i>Phys. Stat. Sol. A</i> , 31, 341-50 (1975) <i>Comment</i> : S, dS. 1.3, 6.6 MeV He, 4.4 MeV N -> Si (Cryst.)	1975-Bulg 0799
1975	Schuch, R. 'Blocking-Effekte Bei Transmission von Alpha-Teilchen Durch Germanium - und Siliziumkristalle' <i>Z. Physik A</i> , 272, 61-66 (1975) <i>Comment</i> : S. 8.8 MeV He -> Si, Ge (Cryst.)	1975-Schu 0516
1976	Grahmann, G. Kalbitzer, S. 'Nuclear and Electronic Stopping Powers of Low Energy Ions with Z <= 10 in Silicon' <i>Nucl. Inst. Methods</i> , 132, 119-23 (1976) <i>Comment</i> : S. 2-60 keV H, He, B, C, N, Ne -> Si	1976-Grah 0871
1977	Holland, O. W. Appleton, B. R. 'Well-Channelled Ions with Greater-Than-Random Energy Loss Rates' <i>IEEE Proc. of 4th Intl. Conf. on Small Accelerators, Denton, Tex.</i> (1977) <i>Comment</i> : S. 1.0 MeV He -> Si <111>	1977-Holl 1257
1977	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. 'Stopping Power for Fast Channeled Alpha Particles in Silicon' <i>Phys. Rev. B</i> , 16, 3880-3886 (1977) <i>Comment</i> : S. 160 MeV He -> Si ([110], [111], And Random)	1977-Jarv 1038

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1977	Thompson, D. A. Robinson, J. E. Walker, R. S. 'Inelastic Stopping of Medium Energy Light Ions in Silicon' <i>Rad. Effects, 32, 169-175 (1977)</i> <i>Comment : dS,R,dR. 10-80 keV H, He, Li, B, C, N, O, Ne -> Si</i>	1977-Thom 1076
1978	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. 'Channeling of Fast Protons, Deuterons and Alpha Particles' <i>Preprint (1978)</i> <i>Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -> Si</i>	1978-Jarv 1148
1978	Oetzmann, H. Kalbitzer, S. '4He Stopping Power Measurements by using Ion Implantation and Backscattering Techniques' <i>Intl. Conf. Ion Beam Modification of Materials, Budapest -d (1978)</i> <i>Comment : S. 0.15-1 MeV He -> C, Ge, Si</i>	1978-Oetz 1134
1978	Rosendahl, E. W. Monkediak, J. 'Measurement of the Energy Loss of Non-Channeled Alpha-Particles in Transmission and Interpretation with the Aid of an Averaged Continuum Potential' <i>Z. Physik A, 285, 33-36 (1978)</i> <i>Comment : S. 8.78 MeV He -> Si</i>	1978-Rose 1125
1979	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. 'Channeling of Fast Protons, Deuterons, and Alpha Particles' <i>Phys. Rev. B, 19, 5559-5577 (1979)</i> <i>Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -> Si</i>	1979-Jarv 1199
1979	Santry, D. C. Werner, R. D. 'Thickness Measurements of Thin Foils using Alpha Particles from 148Gd and 241Am' <i>Nucl. Inst. Methods, 159, 523-527 (1979)</i> <i>Comment : S, dS. 3.138 MeV - 5.486 MeV He -> Be, C, Al, Si, Ni, Ag, Au</i>	1979-Sant3 1350
1980	Oetzmann, H. Kalbitzer, S. 'He4-Stopping Power Measurements by using Ion Implantation and Backscattering Techniques' <i>Rad. Effects, 47, 73-80 (1980)</i> <i>Comment : S, dS. 0-1E5 keV He -> C, Si, Ge</i>	1980-Oetz 1324
1980	Santry, D. C. Werner, R. D. 'Stopping Power Values of Be, C, Al and Si for 4He Ions' <i>Nucl. Inst. Methods, 178, 523-530 (1980)</i> <i>Comment : S. He (0.2-2.0 MeV) -> Be, C, Al, Si</i>	1980-Sant2 1407

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1981	Pearce, J. D. Hart, R. R. 'Stopping Power Measurements in the 20-150 keV Region using Thick Target Backscattering: H and He on C, Si and Au' <i>J. Appl. Phys.</i> , 52, 5056 (1981) <i>Comment</i> : S. H, He (20-150 keV) -> C, Si, Au	1981-Pear 1736
1981	Santry, D. C. Werner, R. D. 'Stopping Power Values of C, Al, Si, Ni, Ag and Au for 3He Ions' <i>Nucl. Inst. Methods</i> , 185, 517-521 (1981) <i>Comment</i> : S. He3 (200-2000 keV) -> C, Al, Si, Ni, Ag, Au	1981-Sant2 1449
1984	Santry, D. C. Werner, R. D. 'Stopping Powers of C, Al, Si, Ti, Ni, Ag, Au and Mylar using Radioactive Alpha Sources' <i>Nucl. Inst. Methods</i> , B1, 13 (1984) <i>Comment</i> : S. He (2-7 MeV) -> > C, Al, Si, Ti, Ni, Ag, Au, Mylar	1984-Sant 1757
1988	Yamaguchi, S. Takahiro, K. Nakajima, H. Fujino, Y. Sagara, S. 'Energy Loss of He Ions in H-Implanted Materials' <i>Nucl. Inst. Methods</i> , B33, 163-167 (1988) <i>Comment</i> : S. He (1.5 MeV) -> Be, Si, Al (doped with H)	1988-Yama 1962
1993	Narumi, K. Fujii, Y. Kishine, K. Fujiwara, S. Kimura, K. 'Energy Losses of 12-32 keV H, He and N Ions at Glancing Angle Scattering from Clean Surfaces of Silicon Crystals' <i>J. Phys. Soc. Jap.</i> , 62, 1603-1611 (1993) <i>Comment</i> : S. H, He, N (12-32 keV) -> Si Surface scattering effects	1993-Naru 2054
1993	Nieman, D. Oberschachtsiek, P. Kalbitzer, S. Zeindl, H. P. 'Energy Loss and Straggling of MeV He-4 Ions in a Si/Sb Multilayer Target' <i>Nucl. Inst. Methods</i> , B80/81, 37-40 (1993) <i>Comment</i> : S, dS. He (0.1-4.0 MeV) -> Si/Sb Layers	1993-Niem 1868
1995	Dos Santos, J. H. R. Grande, P. L. Boudinov, H. Behar, M. Stoll, R. 'Electronic Stopping Power of <100> Axial Channelled He Ions in Si Crystals' <i>Nucl. Inst. Methods</i> , B106, 51-54 (1995) <i>Comment</i> : S. He (0.2-4.5 MeV) -> Si	1995-Dos 1832
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. 'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions' <i>Nucl. Inst. Methods</i> , B115, 315-318 (1996) <i>Comment</i> : S. Channeling of ions He to Kr in Si <110>	1996-Gelf 1814

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1996	Misdaq, M. A. Ellassali, R. 'Average Stopping Powers for Channeled Ions using Computational and Experimental Methods' <i>Nucl. Inst. Methods, 119, 325-330 (1996)</i> <i>Comment : S. Light ions -> Si, GaAs (channeled)</i>	1996-Misd 0964
1996	Niemann, D. Kinac, G. Kalbitzer, S. 'Stopping Power of H, He and N in Si in the Energy Range of 0.02-1.0 MeV/amu' <i>Nucl. Inst. Methods, 118, 11-18 (1996)</i> <i>Comment : S. H, He, N (.02-1.0 MeV/amu) -> Si</i>	1996-Niem 1101
2000	Hoshino, Y. Okazawa, T. Nishii, T. Nishimura, T. Kido, Y. 'Correction of Ziegler's Stopping Powers of Al, Si and their Oxides for MeV He Ions' <i>Nucl. Inst. Methods, B171, 409-413 (2000)</i> <i>Comment : S. He (1.1 - 2.6 MeV) -> Al, Si</i>	2000-Hosh 2344
2002	Azevedo, G. Behar, M. Dias, J. F. Grande, P. L. daSilva, D. L. 'Random and Channeling Stopping Powers of He and Li Ions in Si' <i>Phys. Rev., B-65, 075203-1 - 9 (2002)</i> <i>Comment : S. He, Li -> Si</i>	2002-Azev 3122
2002	Barradas, N. P. Jeynes, C. Webb, R. P. Wendler, E. 'Accurate Determination of the Stopping Power of 4-He in Si using Bayesian Inference' <i>Nucl. Inst. Methods, B194, 15-25 (2002)</i> <i>Comment : S. He -> Si</i>	2002-Barr 3108
2004	Zhang, Y. Weber, W. J. 'Studies of Electronic Stopping Powers using Time of Flight Spectrometry' <i>Nucl. Inst. Methods, B219-220, 256-262 (2004)</i> <i>Comment : S. He, O, Al -> C, SiC</i>	2004-Zha1 3133
2008	Abdesselam, M. Ouichaoui, S. Azzouz, M. Chami, A.C. Siad, M. 'Stopping of 0.3-1.2 MeV/u protons and alpha particles in Si' <i>Nucl. Instrum. Methods Phys. Res. B 266, 3899 (2008)</i> <i>Comment : S. H, He (0.3-1.2 MeV/u) -> Si</i>	2008-Abde 3150